10. The material as defined in claim 1, wherein the polycrystalline gallium-containing group III metal nitride material has a porosity from about 10 percent to about 30 percent by volume.

11. The material as defined in claim 1, wherein each of the plurality of grains is characterized by an average grain diameter in a range of from about 1 millimeter to about 10 micrometers.

12. The material as defined in claim 1, wherein the plurality of grains is characterized by an average grain diameter greater than about 1.0 micrometer.

13. The material as defined in claim 1, wherein the polycrystalline gallium-containing group III metal nitride material is characterized by an apparent density in a range of from about 85 percent to about 95 percent of a theoretical value.

14. The material as defined in claim 1, wherein the atomic fraction of the gallium-containing group III metal in the crystalline gallium-containing group III metal nitride is in a range of from about 0.50 to about 0.51.

15. The material as defined in claim 1, wherein the crystalline gallium-containing group III metal nitride comprises one or more dopants to provide one or more of an n-type material, a p-type material, or a semi-insulating material.

16. The material as defined in claim 15, wherein the one or more of an n-type material, a p-type material, or a semi-insulating material is characterized by a dopant concentration in a range of from about 10^{21} atoms per cubic centimeters to about 10^{16} atoms per cubic centimeters.

17. The material as defined in claim 1, wherein the polycrystalline gallium-containing group III metal nitride material has an inter-grain bend strength greater than about 20 MegaPascal.

18. The material as defined in claim 1, wherein the plurality of inclusions comprise a material selected from a metal, a metal nitride, a metal halide, a metal oxynitride, a metal oxyhalide, a metal oxide, and a combination of any of the foregoing.

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